In the disclosure:

Please change the paragraph at page 1, line 21, as follows:

--As the following consideration shows, such a thin SiO_2 intermediate layer reduces the dielectric effectiveness of the substitute material. If we assume that the thickness $t_{high\text{-}k}$ ~~$t_{high\text{-}k}$~~ of the alternative dielectric is to afford the same capacitance as an SiO_2 layer of the equivalent thickness t_{eq}, that gives:

~~thigh-k = (khigh-k / kSiO2)teq,~~ $t_{high\text{-}k} = (k_{high\text{-}k} / k_{SiO2})\, t_{eq},$ (1)

wherein k_{SiO2} is the dielectric constant of the SiO_2. As the SiO_2 intermediate layer represents a second capacitance C_{SiO2} connected in series with the alternative dielectric, the resulting capacitance can be calculated as follow:

$$1/C_{res} = 1/C_{high\text{-}k} + 1/C_{SiO2}, \qquad (2)$$

wherein $C_{high\text{-}k}$ is the capacitance of the dielectric layer. Using (1), that then gives the following for the equivalent thickness of the layer system t^s_{eq}, comprising a thin SiO_2 layer t_{SiO2} and the dielectric layer $t_{high\text{-}k}$,

$$t^s_{eq} = t_{SiO2} + (k_{SiO2} / k_{high\text{-}k})\, \text{~~}t_{high\text{-}k},\text{~~}\ t_{high\text{-}k}. \qquad (3)\text{--}$$